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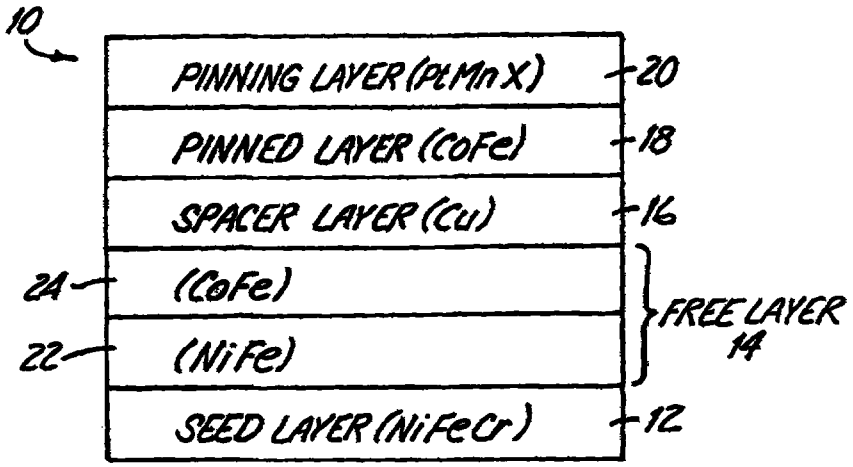
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(57) Abstract

A giant magnetoresistive stack (10) for use in a magnetic read head includes a NiFeCr seed layer (12), a ferromagnetic free layer (14), a nonmagnetic spacer layer (16), a ferromagnetic pinned layer (18), and a PtMnX pinning layer (20), where X is either Cr or Pd. The ferromagnetic free layer (14) has a rotatable magnetic moment and is positioned adjacent to the NiFeCr seed layer (12). The ferromagnetic pinned layer (18) has a fixed magnetic moment and is positioned adjacent to the PtMnX pinning layer (20). The nonmagnetic spacer layer (16) is positioned between the free layer (14) and the pinned layer (18).